

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	I_D max $T_A = +25^\circ\text{C}$
60V	5.0Ω @ $V_{GS} = 10\text{V}$	240mA
	7.5Ω @ $V_{GS} = 5\text{V}$	190mA

Description

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- Power Management Functions
- Backlighting

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

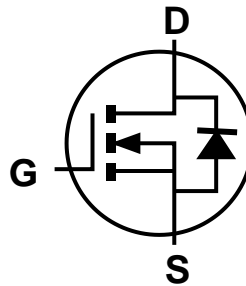
Mechanical Data

- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.006 grams (Approximate)

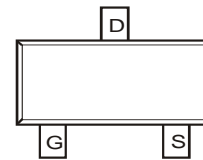
SOT323



Top View



Equivalent Circuit



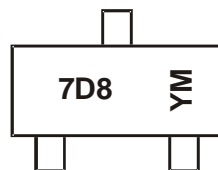
Top View

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN67D8LW-7	SOT323	3000/Tape & Reel
DMN67D8LW-13	SOT323	10000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



7D8= Product Type Marking Code
 YM or YM = Date Code Marking
 Y or Y = Year (ex: B = 2014)
 M = Month (ex: 9 = September)

Date Code Key

Year	2014	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	B	C	D	E	F	G	H	I	J	K	L	M
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	60	V	
Gate-Source Voltage	V _{GSS}	±30	V	
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C	240	mA
		T _A = +70°C	180	
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	0.5	A	
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%) (Note 6)	I _{DM}	0.8	A	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	320	mW
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	398	°C/W
Total Power Dissipation (Note 6)	P _D	470	mW
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	273	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	V _{GS} = 0V, I _D = 10μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1.0	μA	V _{DS} = 60V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1.0	—	2.5	V	V _{DS} = 10V, I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	1.5	5.0	Ω	V _{GS} = 10V, I _D = 0.5A
		—	3.2	7.5		V _{GS} = 5V, I _D = 0.05A
Forward Transfer Admittance	Y _{fs}	80	—	—	mS	V _{DS} = 10V, I _D = 0.2A
Diode Forward Voltage	V _{SD}	—	0.78	1.5	V	V _{GS} = 0V, I _S = 115mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iSS}	—	22	—	pF	V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oSS}	—	4.1	—	pF	
Reverse Transfer Capacitance	C _{rSS}	—	2.5	—	pF	
Gate Resistance	R _g	—	120	—	Ω	f = 1.0MHz, V _{GS} = 0V, V _{DS} = 0V
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	361	—	pC	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 250mA
Total Gate Charge (V _{GS} = 10V)	Q _g	—	821	—	pC	
Gate-Source Charge	Q _{gs}	—	162	—	pC	
Gate-Drain Charge	Q _{gd}	—	116	—	pC	
Turn-On Delay Time	t _{D(ON)}	—	2.8	—	ns	V _{DD} = 30V, I _D = 0.2A, R _L = 150Ω, V _{GS} = 10V, R _G = 25Ω
Turn-On Rise Time	t _R	—	3.0	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	7.6	—	ns	
Turn-Off Fall Time	t _F	—	5.6	—	ns	

- Notes:
- Device mounted on FR-4 PCB, with minimum recommended pad layout
 - Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

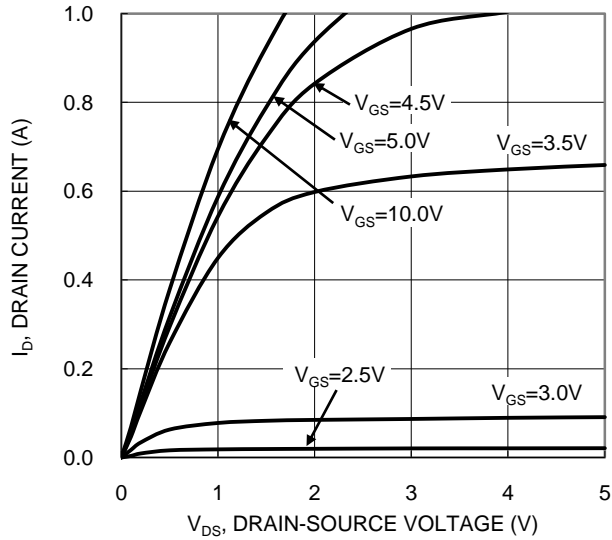


Figure 1. Typical Output Characteristic

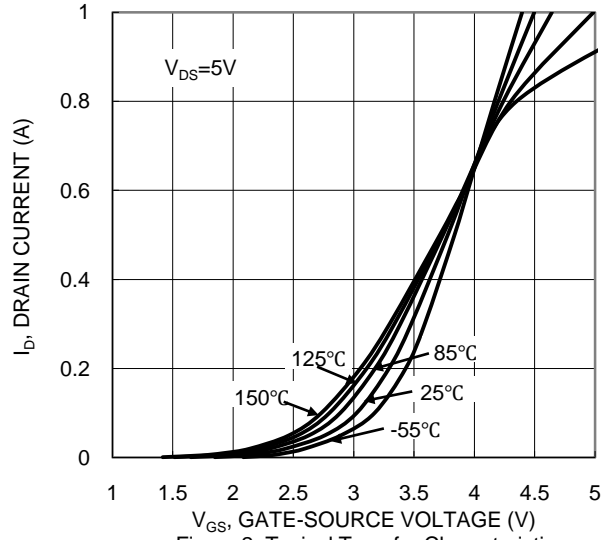


Figure 2. Typical Transfer Characteristic

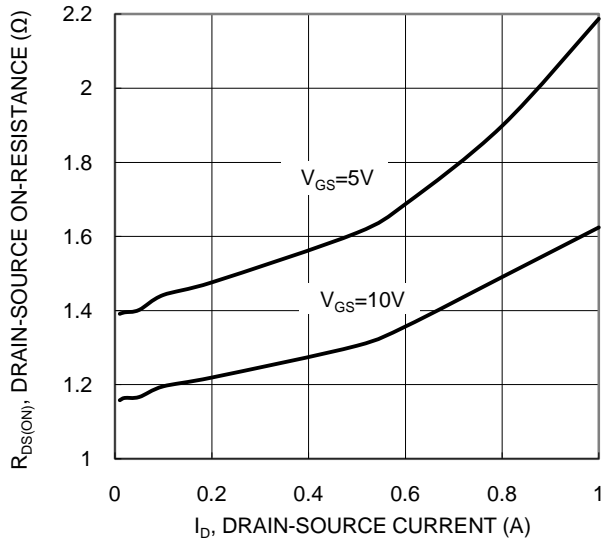


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

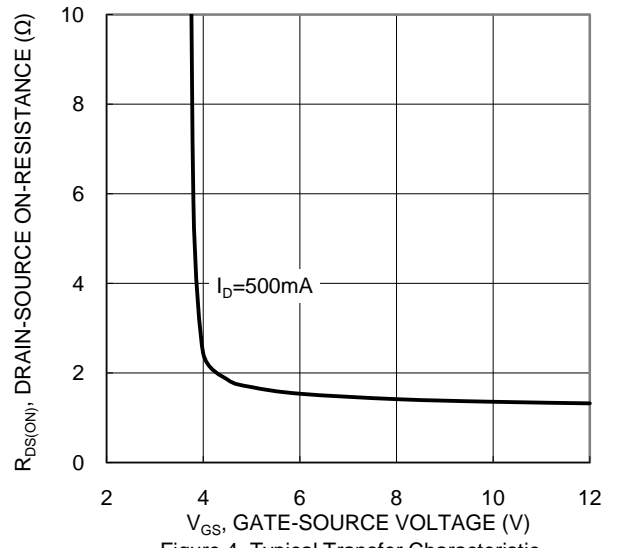


Figure 4. Typical Transfer Characteristic

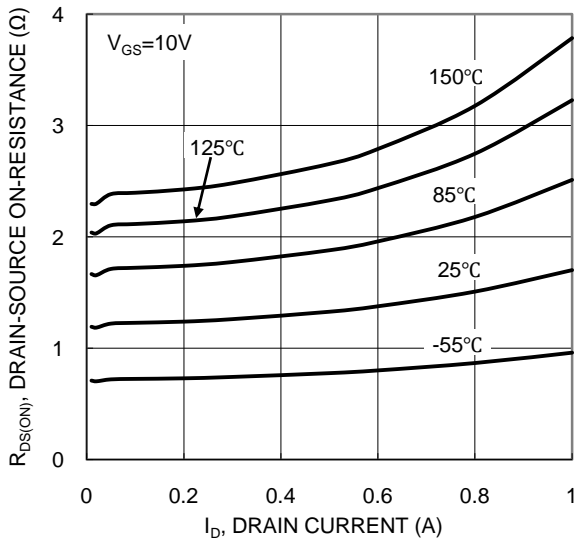


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

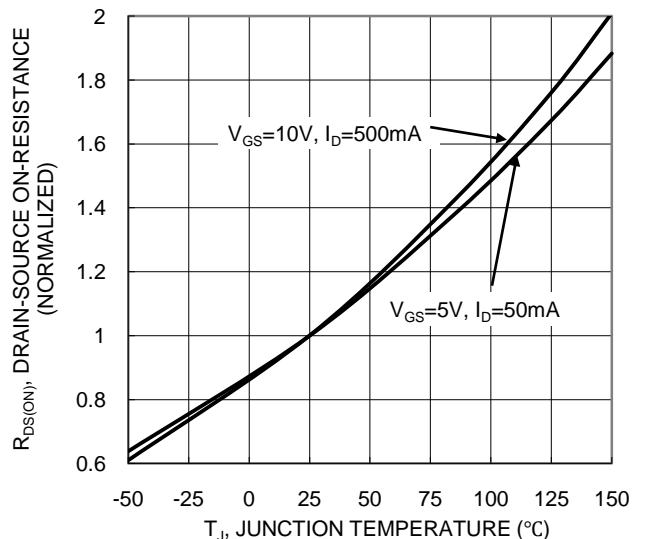


Figure 6. On-Resistance Variation with Junction Temperature

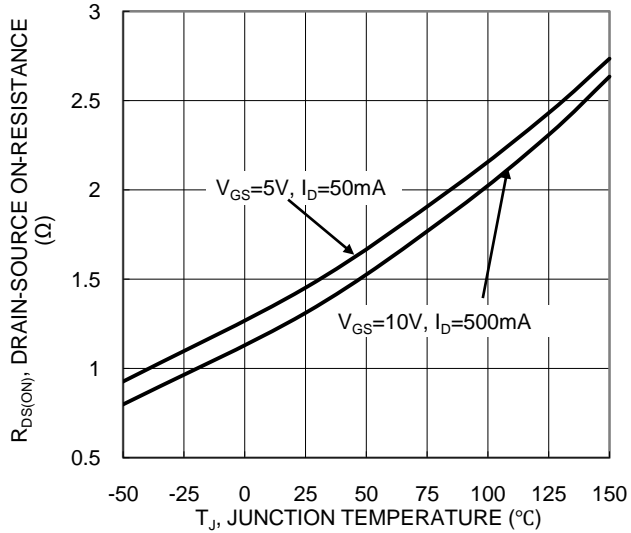


Figure 7. On-Resistance Variation with Junction Temperature

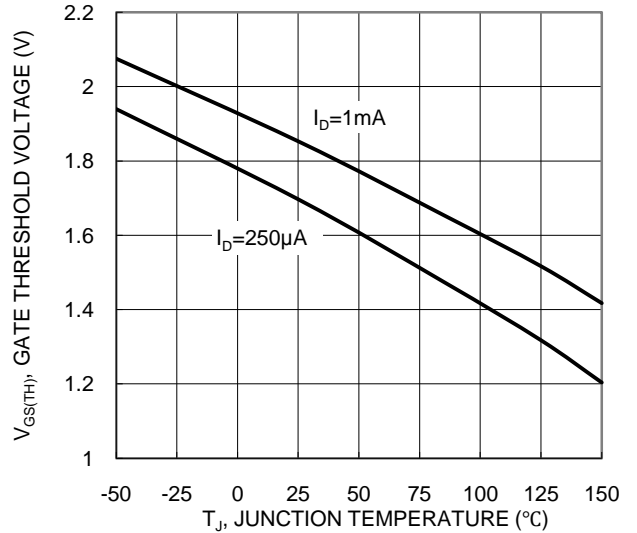


Figure 8. Gate Threshold Variation vs. Junction Temperature

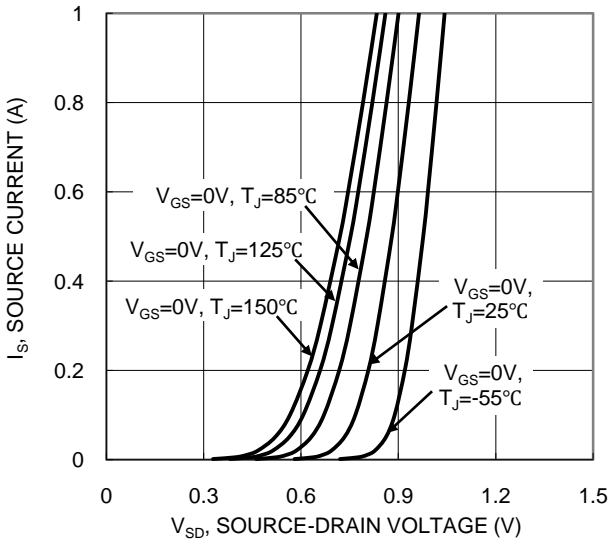


Figure 9. Diode Forward Voltage vs. Current

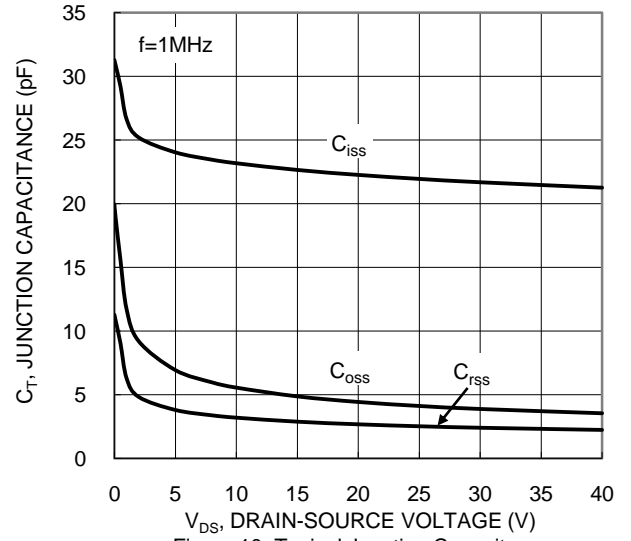


Figure 10. Typical Junction Capacitance

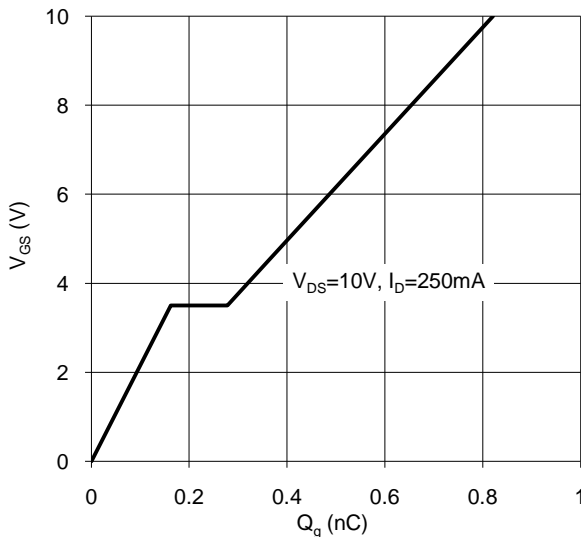


Figure 11. Gate Charge

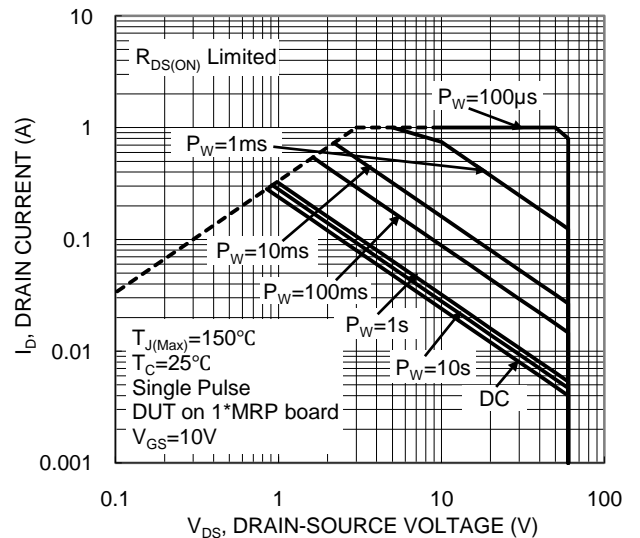
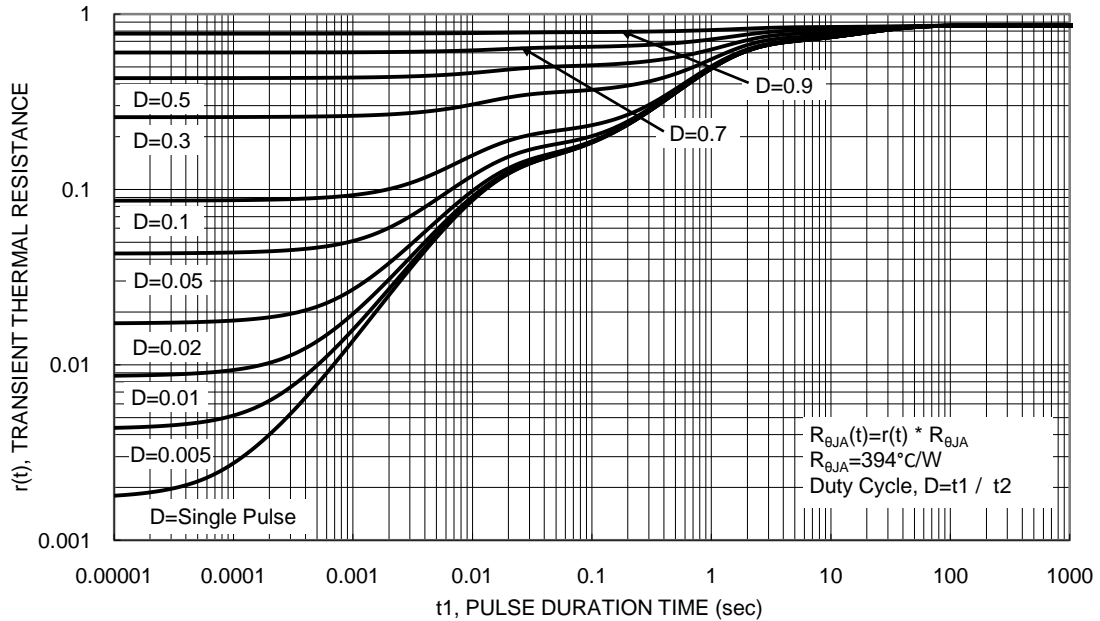
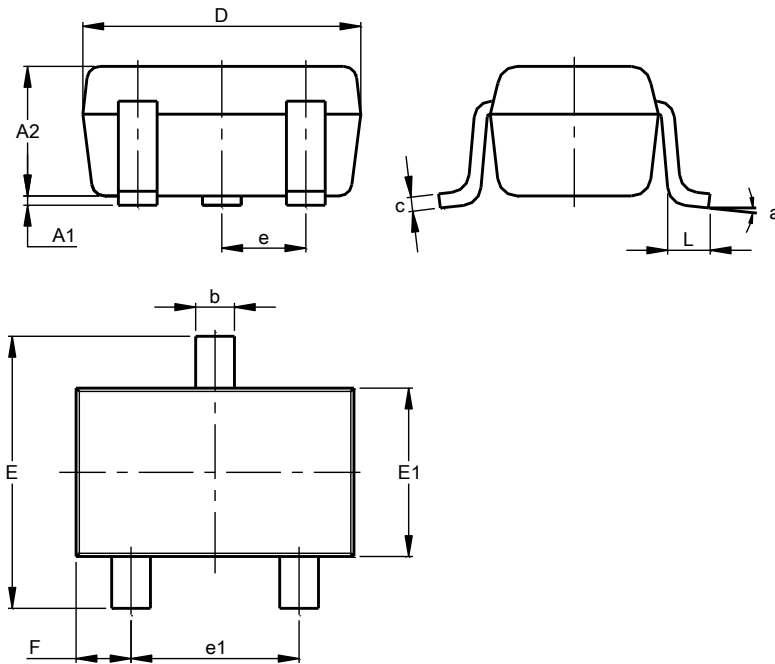


Figure 12. SOA, Safe Operation Area



Package Outline Dimensions

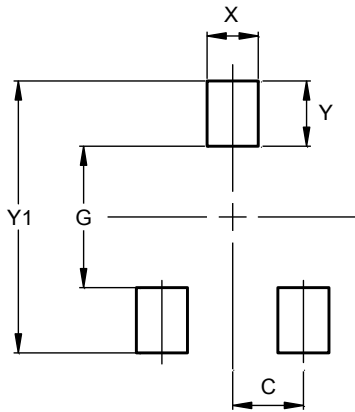
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SOT323			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.25	0.40	0.30
c	0.10	0.18	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
e1	1.20	1.40	1.30
F	0.375	0.475	0.425
L	0.25	0.40	0.30
a	8°		
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500

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